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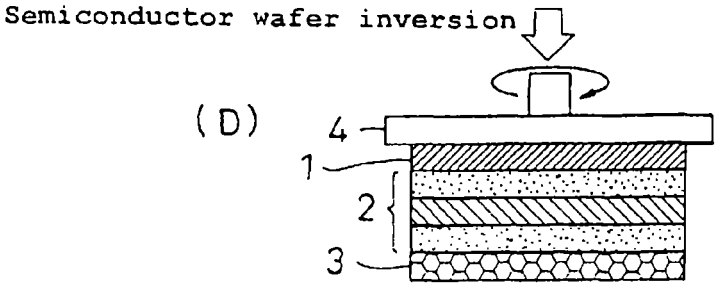
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(54) Title: METHOD OF PROCESSING A SEMICONDUCTOR WAFER



(57) Abstract: The present invention is to provide a method of processing a semiconductor wafer comprising the steps of: sticking a support wafer (3) onto a front surface of a semiconductor wafer (1) having a pattern formed thereon, with a two-sided adhesive sheet (2); and performing a thinning process on a rear surface of the semiconductor wafer. By sticking the support wafer onto the semiconductor wafer with the two-sided adhesive sheet, sufficient strength and rigidity can be obtained even after a thinning process is carried out.

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